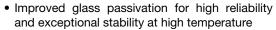


# Medium Power Phase Control Thyristors (Stud Version), 10 A



PRIMARY CHARACTERISTICS				
I <sub>T(AV)</sub>	10 A			
V <sub>DRM</sub> /V <sub>RRM</sub>	100 V, 200 V, 400 V, 600 V, 800 V, 1000 V, 1200 V			
V <sub>TM</sub>	1.75 V			
I <sub>GT</sub>	60 mA			
T <sub>J</sub>	-65 °C to +125 °C			
Package	TO-48 (TO-208AA)			
Circuit configuration	Single SCR			

#### **FEATURES**





- High dl<sub>F</sub>/dt and dV/dt capabilities
- Standard package
- Low thermal resistance
- · Metric threads version available
- Types up to 1200 V V<sub>DRM</sub>/V<sub>RRM</sub>
- Designed and qualified for industrial and consumer level
- Material categorization: for definitions of compliance please see <a href="https://www.vishay.com/doc?99912"><u>www.vishay.com/doc?99912</u></a>

#### **TYPICAL APPLICATIONS**

- Medium power switching
- · Phase control applications

MAJOR RATINGS AND CHARACTERISTICS					
PARAMETER	TEST CONDITIONS	VALUES	UNITS		
1		10	А		
I <sub>T(AV)</sub>	T <sub>C</sub>	85	°C		
I <sub>T(RMS)</sub>		25	А		
I <sub>TSM</sub>	50 Hz	225	А А		
	60 Hz	240			
l <sup>2</sup> t	50 Hz	255	A2-		
1-1	60 Hz	233	A <sup>2</sup> s		
V <sub>DRM</sub> /V <sub>RRM</sub>		100 to 1200	V		
t <sub>q</sub>	Typical	110	μs		
T <sub>J</sub>		-65 to +125	°C		

#### **ELECTRICAL SPECIFICATIONS**

VOLTAGE RATINGS							
TYPE NUMBER	VOLTAGE CODE	V <sub>DRM</sub> /V <sub>RRM</sub> , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE <sup>(1)</sup> V	V <sub>RSM</sub> , MAXIMUM NON-REPETITIVE PEAK VOLTAGE <sup>(2)</sup> V	$I_{DRM}/I_{RRM}$ MAXIMUM AT T <sub>J</sub> = T <sub>J</sub> MAXIMUM mA			
	10	100	150	20			
	20	200	300				
	40	400	500				
VS-10RIA	60	600	700	10			
	80	800	900	10			
	100	1000	1100				
	120	1200	1300				

#### Notes

<sup>(1)</sup> Units may be broken over non-repetitively in the off-state direction without damage, if dl/dt does not exceed 20 A/µs

 $<sup>\</sup>ensuremath{^{(2)}}$  For voltage pulses with  $t_p \leq 5 \ ms$ 



ABSOLUTE MAXIMUM RAT	TINGS					
PARAMETER	SYMBOL		TEST CONDITIONS		VALUES	UNITS
Maximum average on-state current	I	190° conducti	180° conduction, half sine wave		10	Α
at case temperature	I <sub>T(AV)</sub>	100 Conducti	on, nan sine wave		85	°C
Maximum RMS on-state current	I <sub>T(RMS)</sub>				25	Α
		t = 10 ms	No voltage		225	
Maximum peak, one-cycle	L	t = 8.3 ms	reapplied		240	Α
non-repetitive surge current	I <sub>TSM</sub>	t = 10 ms	100 % V <sub>RRM</sub>		190	A
		t = 8.3 ms	reapplied	Sinusoidal half wave,	200	
Maximum I <sup>2</sup> t for fusing		t = 10 ms	No voltage	initial $T_J = T_J$ maximum	255	- A <sup>2</sup> s
	l <sup>2</sup> t	t = 8.3 ms	reapplied		233	
	i-r	t = 10 ms	100 % V <sub>RRM</sub> reapplied		180	
		t = 8.3 ms			165	
Maximum I <sup>2</sup> √t for fusing	I²√t	t = 0.1 to 10 m	t = 0.1 to 10 ms, no voltage reapplied		2550	A²√s
Low level value of threshold voltage	V <sub>T(TO)1</sub>	(16.7 % x π x	(16.7 % x $\pi$ x $I_{T(AV)} < I < \pi$ x $I_{T(AV)}$ ), $T_J = T_J$ maximum		1.10	V
High level value of threshold voltage	V <sub>T(TO)2</sub>	$(I > \pi \times I_{T(AV)}),$	$T_J = T_J \text{ maximum}$		1.39	V
Low level value of on-state slope resistance	r <sub>t1</sub>	(16.7 % x π x	(16.7 % x $\pi$ x $I_{T(AV)}$ < I < $\pi$ x $I_{T(AV)}$ ), $T_J = T_J$ maximum		24.3	mΩ
High level value of on-state slope resistance	r <sub>t2</sub>	$(I > \pi \times I_{T(AV)}), T_J = T_J \text{ maximum}$		16.7	11152	
Maximum on-state voltage	$V_{TM}$	$I_{pk}$ = 32 A, $T_J$ = 25 °C, $t_p$ = 10 ms sine pulse		1.75	V	
Maximum holding current	I <sub>H</sub>	T. = 25 °C 22	odo supply 12 V ro	esistivo load	130	mΛ
Typical latching current	ΙL	1j = 25 C, all	ode supply 12 V re	SISTING TOAU	200	mA

SWITCHING					
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS
	$V_{DRM} \le 600 \text{ V}$			200	
Maximum rate of rise V <sub>DRM</sub> ≤ 800 V		41 /d+	$T_J = T_J$ maximum, $V_{DM} = Rated V_{DRM}$ $Gate pulse = 20 V, 15 Ω, t_p = 6 μs, t_r = 0.1 μs maximum$ $I_{TM} = (2 x rated dl/dt) A$	180	- A/μs
of turned-on current	urned-on current $V_{DRM} \le 1000 \text{ V}$			160	
$V_{DRM} \le 1600 \text{ V}$			,	150	
Typical turn-on time		t <sub>gt</sub>	$T_J = 25$ °C, at rated $V_{DRM}/V_{RRM}$ , $T_J = 125$ °C	0.9	
Typical reverse recovery time		t <sub>rr</sub>	$T_J = T_J$ maximum, $I_{TM} = I_{T(AV)}$ , $t_p > 200 \mu s$ , $dI_F/dt = -10 A/\mu s$	4	μs
Typical turn-off time		tq	$T_J = T_J$ maximum, $I_{TM} = I_{T(AV)}$ , $t_p > 200~\mu$ s, $V_R = 100~V$ , $dI_F/dt = -10~A/\mu$ s, $dV/dt = 20~V/\mu$ s linear to 67 % $V_{DRM}$ , gate bias 0 V to 100 W	110	μο

#### Note

•  $t_q = 10 \mu s$  up to 600 V,  $t_q = 30 \mu s$  up to 1600 V available on special request

BLOCKING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum critical rate of rise	dV/dt	$T_J = T_J$ maximum linear to 100 % rated $V_{DRM}$	100	V/µs
of off-state voltage	uv/ut	$T_J = T_J$ maximum linear to 67 % rated $V_{DRM}$	300 (1)	ν/μ5

#### Note

 $^{(1)}$  Available with:  $dV/dt = 1000 V/\mu s$ , to complete code add S90 i.e. 10RIA120S90



TRIGGERING					
PARAMETER	SYMBOL	TE	ST CONDITIONS	VALUES	UNITS
Maximum peak gate power	P <sub>GM</sub>	T - T movimum		8.0	W
Maximum average gate power	P <sub>G(AV)</sub>	$T_J = T_J$ maximum		2.0	۷V
Maximum peak positive gate current	$I_{GM}$	$T_J = T_J$ maximum		1.5	Α
Maximum peak negative gate voltage	-V <sub>GM</sub>	$T_J = T_J$ maximum		10	V
	I <sub>GT</sub>	T <sub>J</sub> = -65 °C	Maximum required gate trigger current/voltage are the lowest value which will trigger all units 6 V anode to cathode applied	90	mA
DC gate current required to trigger		T <sub>J</sub> = 25 °C		60	
		T <sub>J</sub> = 125 °C		35	
		T <sub>J</sub> = -65 °C		3.0	V
DC gate voltage required to trigger	$V_{GT}$	T <sub>J</sub> = 25 °C		2.0	
		T <sub>J</sub> = 125 °C		1.0	
DC gate current not to trigger	$I_{GD}$	T <sub>J</sub> = T <sub>J</sub> maximum, V <sub>DRM</sub> = Rated value		2.0	mA
DC gate voltage not to trigger	$V_GD$	$T_J = T_J$ maximum, $V_{DRM} = Rated value$	Maximum gate current/voltage not to trigger is the maximum value which will not trigger any unit with rated V <sub>DRM</sub> anode to cathode applied	0.2	V

THERMAL AND MECHANICAL SPECIFICATIONS					
PARAMETER	SYMBOL	TEST CONDITIONS	VAL	VALUES	
Maximum operating junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-65 to	+125	°C
Maximum thermal resistance, junction to case	R <sub>thJC</sub>	DC operation	1.	1.85	
Maximum thermal resistance, case to heat sink	R <sub>thCS</sub>	Mounting surface, smooth, flat and greased 0.35		35	K/W
			TO NUT	TO DEVICE	
			20 (27.5)	25	lbf ⋅ in
Mounting torque		Lubricated threads (Non-lubricated threads)	0.23 (0.32)	0.29	kgf · m
		(1011) (1211) (111)	2.3 (3.1)	2.8	N · m
Approximate weight			14		g
Approximate weight			0.	49	OZ.
Case style		See dimensions - link at the end of datasheet	TO	-48 (TO-208A	A)

△R <sub>thJC</sub> CONDUCTION				
CONDUCTION ANGLE	SINUSOIDAL CONDUCTION	RECTANGULAR CONDUCTION	TEST CONDITIONS	UNITS
180°	0.44	0.32		
120°	0.53	0.56		
90°	0.68	0.75	$T_J = T_J$ maximum	K/W
60°	1.01	1.05		
30°	1.71	1.73		

#### Note

The table above shows the increment of thermal resistance R<sub>thJC</sub> when devices operate at different conduction angles than DC



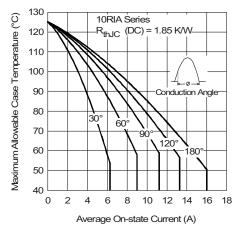


Fig. 1 - Current Ratings Characteristics

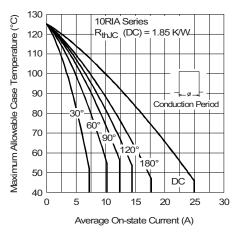


Fig. 2 - Current Ratings Characteristics

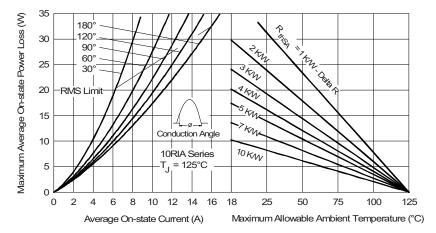


Fig. 3 - On-State Power Loss Characteristics

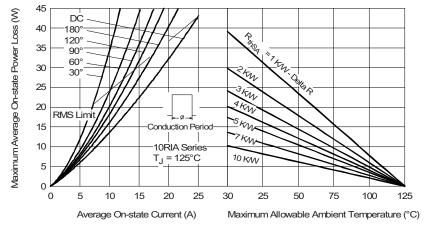


Fig. 4 - On-State Power Loss Characteristics



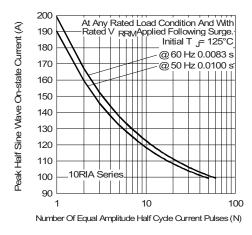


Fig. 5 - Maximum Non-Repetitive Surge Current

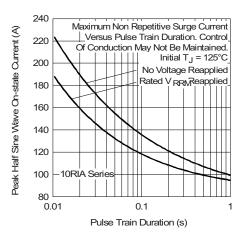


Fig. 6 - Maximum Non-Repetitive Surge Current

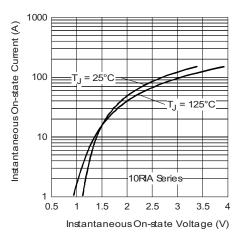


Fig. 7 - Forward Voltage Drop Characteristics

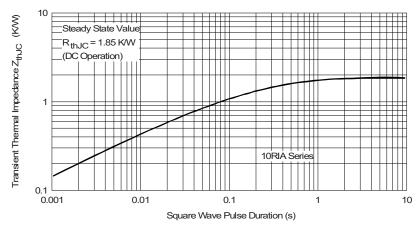


Fig. 8 - Thermal Impedance  $Z_{thJC}$  Characteristics



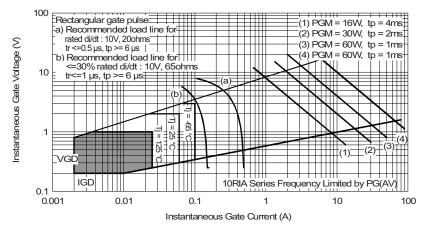
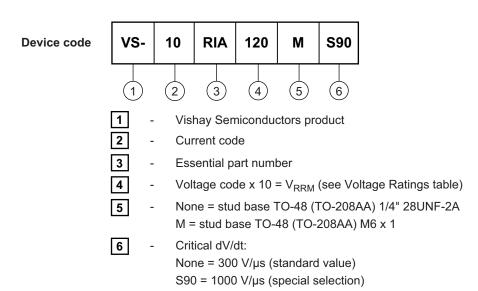


Fig. 9 - Gate Characteristics

#### **ORDERING INFORMATION TABLE**

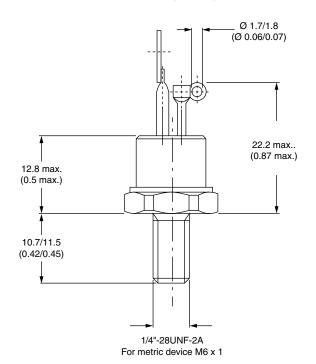


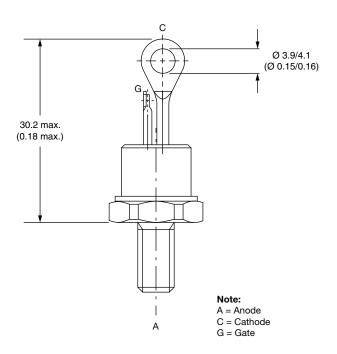
LINKS TO RELAT	ED DOCUMENTS
Dimensions	www.vishay.com/doc?95333

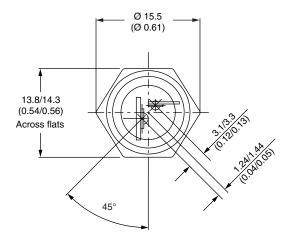


# TO-208AA (TO-48)

### **DIMENSIONS** in millimeters (inches)









## **Legal Disclaimer Notice**

Vishay

## **Disclaimer**

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Hyperlinks included in this datasheet may direct users to third-party websites. These links are provided as a convenience and for informational purposes only. Inclusion of these hyperlinks does not constitute an endorsement or an approval by Vishay of any of the products, services or opinions of the corporation, organization or individual associated with the third-party website. Vishay disclaims any and all liability and bears no responsibility for the accuracy, legality or content of the third-party website or for that of subsequent links.

Vishay products are not designed for use in life-saving or life-sustaining applications or any application in which the failure of the Vishay product could result in personal injury or death unless specifically qualified in writing by Vishay. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.